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## BD243B/BD243C BD244B/BD244C

## COMPLEMENTARY SILICON POWER TRANSISTORS

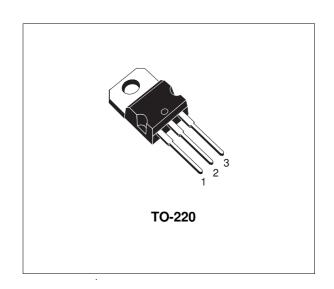
 STMicroelectronics PREFERRED SALESTYPES

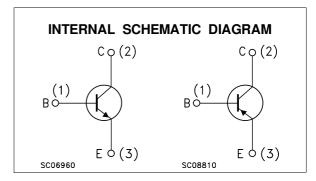
#### **DESCRIPTION**

The BD243B and BD243C are silicon Epitaxial-Base NPN transistors mounted in Jedec TO-220 plastic package.

They are inteded for use in medium power linear and switching applications.

The complementary PNP types are BD244B and BD244C respectively.





#### **ABSOLUTE MAXIMUM RATINGS**

Symbol	Parameter		Va	Unit	
		NPN	BD243B	BD243C	
		PNP	BD244B	BD244C	
V <sub>CBO</sub>	Collector-Base Voltage (I <sub>E</sub> = 0)		80	100	V
V <sub>CEO</sub>	Collector-Emitter Voltage (I <sub>B</sub> = 0)		80	100	V
$V_{EBO}$	Emitter-Base Voltage (I <sub>C</sub> = 0)		Ę	5	V
Ic	Collector Current		(	6	Α
I <sub>CM</sub>	Collector Peak Current		1	0	Α
$I_{B}$	Base Current		2	2	Α
P <sub>tot</sub>	Total Dissipation at T <sub>c</sub> ≤ 25 °C		6	5	W
T <sub>stg</sub>	Storage Temperature		-65 to	o 150	°C
Tj	Max. Operating Junction Temperature		15	°C	

For PNP types voltage and current values are negative.

September 1999

#### BD243B / BD243C / BD244B / BD244C

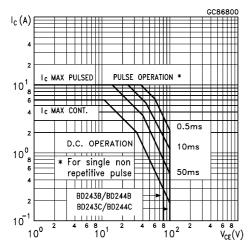
#### THERMAL DATA

R <sub>thj-case</sub>	Thermal Resistance Junction-case	Max	1.92	°C/W
$R_{thj-amb}$	Thermal Resistance Junction-ambient	Max	62.5	°C/W

### **ELECTRICAL CHARACTERISTICS** (T<sub>case</sub> = 25 °C unless otherwise specified)

Symbol	Parameter	Te	st Conditions	Min.	Тур.	Max.	Unit
I <sub>CES</sub>	Collector Cut-off Current (V <sub>BE</sub> = 0)	V <sub>CE</sub> = rated \	/ <sub>CEO</sub>			0.4	mA
I <sub>CEO</sub>	Collector Cut-off Current (I <sub>B</sub> = 0)	V <sub>CE</sub> = 60 V				0.7	mA
I <sub>EBO</sub>	Emitter Cut-off Current (I <sub>C</sub> = 0)	$V_{EB} = 5 V$				1	mA
V <sub>CEO(sus)</sub> *	Collector-Emitter Sustaining Voltage (I <sub>B</sub> = 0)	I <sub>C</sub> = 30 mA for <b>BD243B</b> /I for <b>BD243C</b> /I		80 100			V V
V <sub>CE(sat)</sub> *	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 6 A	I <sub>B</sub> = 1 A			1.5	V
$V_{BE}*$	Base-Emitter Voltage	I <sub>C</sub> = 6 A	$V_{CE} = 4 V$			2	V
h <sub>FE</sub> *	DC Current Gain	I <sub>C</sub> = 0.3 A I <sub>C</sub> = 3 A		30 15			
h <sub>fe</sub>	Small Signal Current Gain	_	V <sub>CE</sub> = 10 V f = 1MHz V <sub>CE</sub> = 10 V f = 1KHz	3 20			

### Safe Operating Area

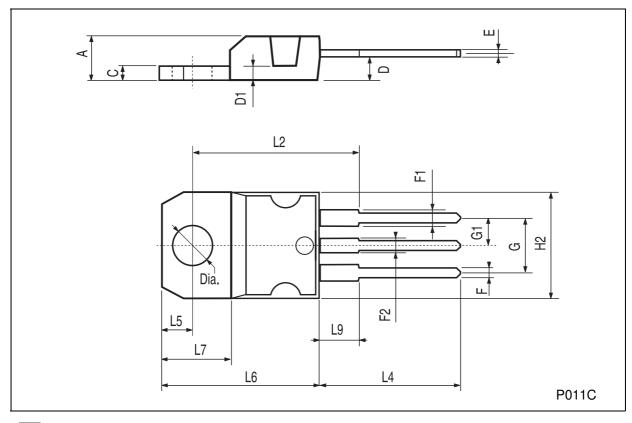


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<sup>\*</sup> Pulsed: Pulse duration = 300  $\mu$ s, duty cycle  $\leq$  2 % For PNP types voltage and current values are negative.

### **TO-220 MECHANICAL DATA**

DIM.		mm			inch	
DINI.	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
Α	4.40		4.60	0.173		0.181
С	1.23		1.32	0.048		0.051
D	2.40		2.72	0.094		0.107
D1		1.27			0.050	
E	0.49		0.70	0.019		0.027
F	0.61		0.88	0.024		0.034
F1	1.14		1.70	0.044		0.067
F2	1.14		1.70	0.044		0.067
G	4.95		5.15	0.194		0.203
G1	2.4		2.7	0.094		0.106
H2	10.0		10.40	0.393		0.409
L2		16.4			0.645	
L4	13.0		14.0	0.511		0.551
L5	2.65		2.95	0.104		0.116
L6	15.25		15.75	0.600		0.620
L7	6.2		6.6	0.244		0.260
L9	3.5		3.93	0.137		0.154
DIA.	3.75		3.85	0.147		0.151



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